



Glass MELF Switching Diode

Qualified per MIL-PRF-19500/116

Qualified Levels:
JAN, JANTX, and
JANTXV

DESCRIPTION

This popular 1N4148UR-1 JEDEC registered switching/signal diode features internal metallurgical bonded construction for military grade products per MIL-PRF-19500/116. Previously listed as a CDLL4148 this small low capacitance diode, with very fast switching speeds, is hermetically sealed and bonded into a double-plug DO-213AA package. It may be used in a variety of very high speed applications including switchers, detectors, transient OR'ing, logic arrays, blocking, as well as low-capacitance steering diodes, etc. Microsemi also offers a variety of other switching/signal diodes.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- Surface mount equivalent of popular JEDEC registered 1N4148 number.
- Hermetically sealed glass construction.
- Metallurgically bonded.
- Double plug construction.
- Very low capacitance.
- Very fast switching speeds with minimal reverse recovery times.
- JAN, JANTX, and JANTXV qualification is available per MIL-PRF-19500/116. (See [part nomenclature](#) for all available options.)
- RoHS compliant version available (commercial grade only).

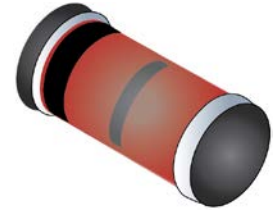
APPLICATIONS / BENEFITS

- High frequency data lines.
- Small size for high density mounting using the surface mount method (see package illustration).
- RS-232 & RS-422 interface networks.
- Ethernet 10 Base T.
- Low capacitance steering or blocking.
- LAN.
- Computers.

MAXIMUM RATINGS @ 25 °C


Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T _J & T _{STG}	-65 to +175	°C
Thermal Resistance Junction-to-Ambient ⁽¹⁾	R _{θJA}	325	°C/W
Thermal Resistance Junction-to-Endcap ⁽²⁾	R _{θJEC}	100	°C/W
Maximum Breakdown Voltage	V _(BR)	100	V
Working Peak Reverse Voltage	V _{RWM}	75	V
Average Rectified Current @ T _A = 75 °C ⁽³⁾	I _O	200	mA
Non-Repetitive Sinusoidal Surge Current (tp = 8.3 ms)	I _{FSM}	2	A (pk)

- NOTES:**
1. T_A = +75°C on printed circuit board (PCB), PCB = FR4 - .0625 inch (1.59 mm) 1-layer 1-Oz Cu, horizontal, in still air; pads = .061 inch (1.55 mm) x .105 inch (2.67 mm); R_{θJA} with a defined PCB thermal resistance condition included, is measured at I_O = 200 mA dc.
 2. See [Figure 2](#) for thermal impedance curves.
 3. See [Figure 1](#) for derating.




DO-213AA Package

Also available in:

DO-35 package
(axial-leaded)
 [1N4148-1](#)

UB package
(surface mount)
 [1N4148UB](#)

UB2 package
(2-Pin surface mount)
 [1N4148UB2](#)

UBC package
(Ceramic Lid surface mount)
 [1N4148UBC](#)

MSC – Lawrence

6 Lake Street,
Lawrence, MA 01841
Tel: 1-800-446-1158 or
(978) 620-2600
Fax: (978) 689-0803

MSC – Ireland

Gort Road Business Park,
Ennis, Co. Clare, Ireland
Tel: +353 (0) 65 6840044
Fax: +353 (0) 65 6822298

Website:

www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Hermetically sealed glass case package.
- TERMINALS: Tin/lead plated or RoHS compliant matte-tin (on commercial grade only) over copper clad steel. Solderable per MIL-STD-750, method 2026.
- POLARITY: Cathode end is banded.
- MOUNTING: The axial coefficient of expansion (COE) of this device is approximately +6PPM/°C. The COE of the mounting surface system should be selected to provide a suitable match with this device.
- MARKING: Part number.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: 0.2 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE
JAN 1N4148 UR -1 (e3)
Reliability Level

JAN = JAN level
 JANTX = JANTX level
 JANTXV = JANTXV level
 See **1N6642US** for JANS level
 Blank = Commercial grade

JEDEC type number

(see [Electrical Characteristics](#) table)

RoHS Compliance

e3 = RoHS compliant (on commercial grade only)
 Blank = non-RoHS compliant

Metallurgically Bonded
MELF Surface Mount
SYMBOLS & DEFINITIONS

Symbol	Definition
I_R	Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.
I_o	Average Rectified Forward Current: The output current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle.
t_{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.
V_F	Forward Voltage: The forward voltage the device will exhibit at a specified current (typically shown as maximum value).
V_R	Reverse Voltage: The reverse voltage dc value, no alternating component.
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range excluding all transient voltages (ref JESD282-B). Also sometimes known as PIV.

ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise noted

FORWARD VOLTAGE V_{F1} @ $I_F=10$ mA	FORWARD VOLTAGE V_{F2} @ $I_F=100$ mA	REVERSE RECOVERY TIME t_{rr} (Note 1)	FORWARD RECOVERY TIME t_{fr} (Note 2)	REVERSE CURRENT I_{R1} @ 20 V	REVERSE CURRENT I_{R2} @ 75 V	REVERSE CURRENT I_{R3} @ 20 V $T_A=150^\circ\text{C}$	REVERSE CURRENT I_{R4} @ 75 V $T_A=150^\circ\text{C}$	CAPACITANCE C (Note 3)	CAPACITANCE C (Note 4)
V	V	ns	ns	nA	μA	μA	μA	pF	pF
0.8	1.2	5	20	25	0.5	35	75	4.0	2.8

NOTE 1: $I_F = I_R = 10$ mA, $R_L = 100$ Ohms.

NOTE 2: $I_F = 50$ mA.

NOTE 3: $V_R = 0$ V, $f = 1$ MHz, $V_{SIG} = 50$ mV (pk to pk).

NOTE 4: $V_R = 1.5$ V, $f = 1$ MHz, $V_{SIG} = 50$ mV (pk to pk).

GRAPHS

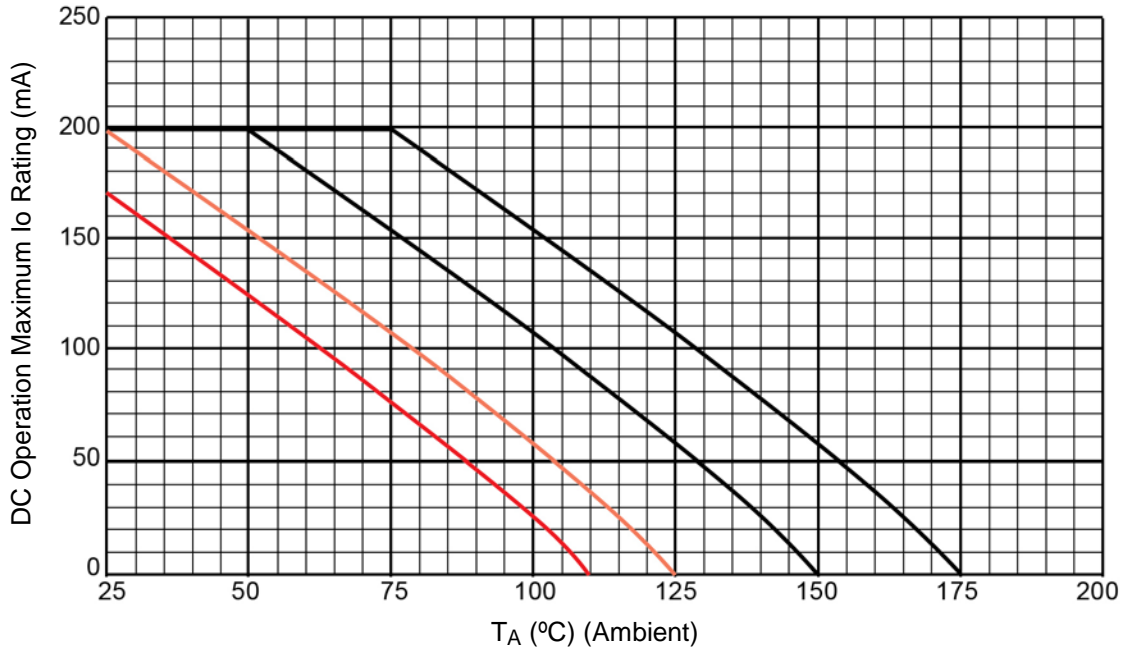


FIGURE 1 – Temperature – Current Derating

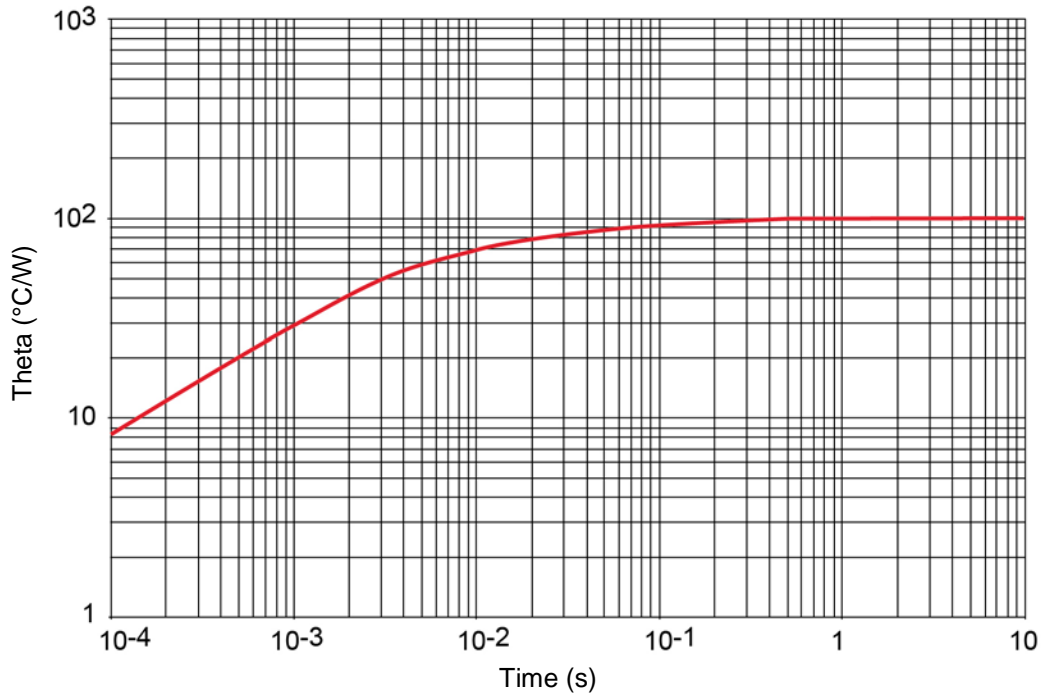


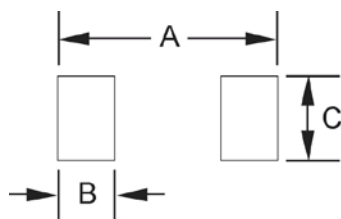
FIGURE 2 – Thermal Impedance

PACKAGE DIMENSIONS


DIM	INCH		MILLIMETERS	
	MIN	MAX	MIN	MAX
BD	0.063	0.067	1.60	1.70
BL	0.130	0.146	3.30	3.71
ECT	0.016	0.022	0.41	0.56
S	.001 min		0.03 min	

NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Dimensions are pre-solder dip.
3. Referencing to dimension S, minimum clearance of glass body to mounting surface on all orientations.
4. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

PAD LAYOUT


	INCH	mm
A	.200	5.08
B	.055	1.40
C	.080	2.03

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Small Signal Switching Diodes](#) category:

Click to view products by [Microchip](#) manufacturer:

Other Similar products are found below :

[BAS16E6433HTMA1](#) [SHN2D02FUTW1T1G](#) [BAS 16-02L E6327](#) [BAS 16-02V H6327](#) [BAS 21U E6327](#) [BAS 28 E6327](#) [BAW56DWQ-7-F](#)
[BAW56M3T5G](#) [IDW40E65D1](#) [IDW40E65D2](#) [SMMSD4148T3G](#) [NSVDAN222T1G](#) [CDSZC01100-HF](#) [BAS28-7](#) [JANTX1N6640](#)
[BAW56HDW-13](#) [BAV99TQ-13-F](#) [SMSD1002T1G](#) [LS4148](#) [IDV15E65D2](#) [W0503RH200S0L](#) [M0268SJ200NLF](#) [M0268RJ200NLF](#)
[DAN217U-TP](#) [BAV21W-HE3_A-08](#) [BAV99-HE3_A-08](#) [BAW56-HE3_A-08](#) [BAS16-HE3_A-08](#) [BAS16D-HE3_A-08](#) [BAV19W-HE3_A-08](#)
[BAS20-HE3_A-08](#) [BAL99-HE3_A-08](#) [BAV23C-HE3_A-08](#) [DHVSD3004BRM-7](#) [DLLFSD01LP3Q-7](#) [BAS16VVQ-7](#)
[IDWD100E120D7XKSA1](#) [IDWD120E120D7XKSA1](#) [IDWD140E120D7XKSA1](#) [IDWD30E120D7XKSA1](#) [IDWD40E120D7XKSA1](#)
[IDWD50E120D7XKSA1](#) [IDWD60E120D7XKSA1](#) [IDWD75E120D7XKSA1](#) [BAS21TWQ-7](#) [BAV21WQ-7-F](#) [MMBD4448HADWQ-7-F](#)
[BAV23AQ-13-F](#) [1N4148WSQ-13-F](#) [BAW56WQ-7-F](#)